

NTJD1155L

MOSFET – Power, P-Channel, High Side Load Switch with Level-Shift, SC-88 8 V, ±1.3 A

The NTJD1155L integrates a P and N-Channel MOSFET in a single package. This device is particularly suited for portable electronic equipment where low control signals, low battery voltages and high load currents are needed. The P-Channel device is specifically designed as a load switch using ON Semiconductor state-of-the-art trench technology. The N-Channel, with an external resistor (R1), functions as a level-shift to drive the P-Channel. The N-Channel MOSFET has internal ESD protection and can be driven by logic signals as low as 1.5 V. The NTJD1155L operates on supply lines from 1.8 to 8.0 V and can drive loads up to 1.3 A with 8.0 V applied to both V_{IN} and $V_{ON/OFF}$.

Features

- Extremely Low $R_{DS(on)}$ P-Channel Load Switch MOSFET
- Level Shift MOSFET is ESD Protected
- Low Profile, Small Footprint Package
- V_{IN} Range 1.8 to 8.0 V
- ON/OFF Range 1.5 to 8.0 V
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating		Symbol	Value	Unit
Input Voltage (V_{DSS} , P-Ch)		V_{IN}	8.0	V
ON/OFF Voltage (V_{GS} , N-Ch)		$V_{ON/OFF}$	8.0	V
Continuous Load Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	I_L	±1.3
		$T_A = 85^\circ\text{C}$		±0.9
Power Dissipation (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	P_D	0.40
		$T_A = 85^\circ\text{C}$		0.20
Pulsed Load Current	$t_p = 10 \mu\text{s}$	I_{LM}	±3.9	A
Operating Junction and Storage Temperature		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$
Source Current (Body Diode)		I_S	-0.4	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	320	$^\circ\text{C}/\text{W}$
Junction-to-Foot – Steady State (Note 1)	$R_{\theta JF}$	220	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

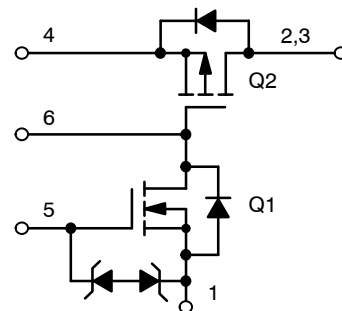


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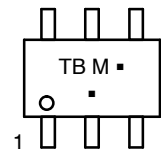
$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D MAX
8.0 V	130 m Ω @ -4.5 V	±1.3 A
	170 m Ω @ -2.5 V	
	260 m Ω @ -1.8 V	

SIMPLIFIED SCHEMATIC



SC-88
(SOT-363)
CASE 419B
STYLE 30

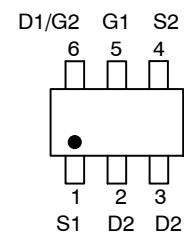
MARKING DIAGRAM



TB = Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

PIN ASSIGNMENT



ORDERING INFORMATION

Device	Package	Shipping†
NTJD1155LT1G, NTJD1155LT2G	SC-88 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTJD1155L

1. Surface-mounted on FR4 board using 1 inch sq pad size
(Cu area = 1.127 in sq [1 oz] including traces).

NTJD1155L

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Q2 Drain-to-Source Breakdown Voltage	V_{IN}	$V_{GS2} = 0\text{ V}, I_{D2} = 250\ \mu\text{A}$	-8.0			V
Forward Leakage Current	I_{FL}	$V_{GS1} = 0\text{ V}, V_{DS2} = -8.0\text{ V}$	$T_J = 25^\circ\text{C}$		1.0	μA
			$T_J = 125^\circ\text{C}$		10	
Q1 Gate-to-Source Leakage Current	I_{GSS}	$V_{DS1} = 0\text{ V}, V_{GS1} = \pm 8.0\text{ V}$			± 100	nA
Q1 Diode Forward On-Voltage	V_{SD}	$I_S = -0.4\text{ A}, V_{GS1} = 0\text{ V}$		-0.8	-1.1	V

ON CHARACTERISTICS

ON/OFF Voltage	$V_{ON/OFF}$		1.5		8.0	V	
Q1 Gate Threshold Voltage	$V_{GS1(th)}$	$V_{GS1} = V_{DS1}, I_D = 250\ \mu\text{A}$	0.4		1.0	V	
Input Voltage	V_{IN}	$V_{GS1} = V_{DS1}, I_D = 250\ \mu\text{A}$	1.8		8.0	V	
Q2 Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{ON/OFF} = 1.5\text{ V}$	$V_{IN} = 4.5\text{ V}, I_L = 1.2\text{ A}$		130	175	$\text{m}\Omega$
			$V_{IN} = 2.5\text{ V}, I_L = 1.0\text{ A}$		170	220	
			$V_{IN} = 1.8\text{ V}, I_L = 0.7\text{ A}$		260	320	
Load Current	I_L	$V_{DROP} \leq 0.2\text{ V}, V_{IN} = 5.0\text{ V}, V_{ON/OFF} = 1.5\text{ V}$	1.0			A	
		$V_{DROP} \leq 0.3\text{ V}, V_{IN} = 2.5\text{ V}, V_{ON/OFF} = 1.5\text{ V}$	1.0				

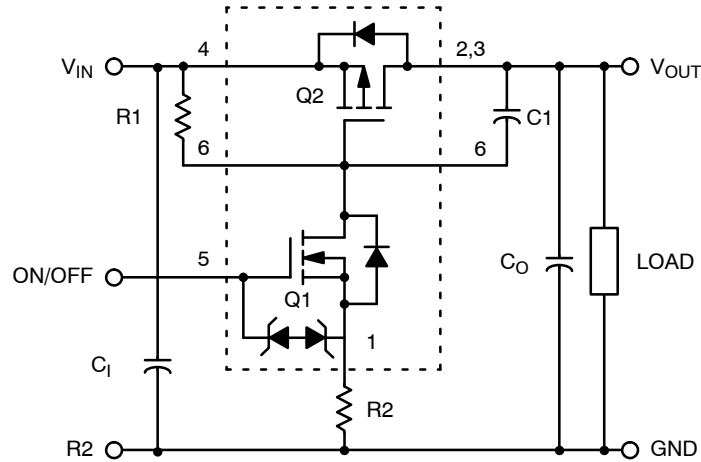


Figure 1. Load Switch Application

Components	Description	Values
R1	Pullup Resistor	Typical 10 k Ω to 1.0 M Ω *
R2	Optional Slew-Rate Control	Typical 0 to 100 k Ω *
C_0, C_1	Output Capacitance	Usually < 1.0 μF
C1	Optional In-Rush Current Control	Typical $\leq 1000\ \text{pF}$

*Minimum R1 value should be at least 10 x R2 to ensure Q1 turn-on.

NTJD1155L

TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

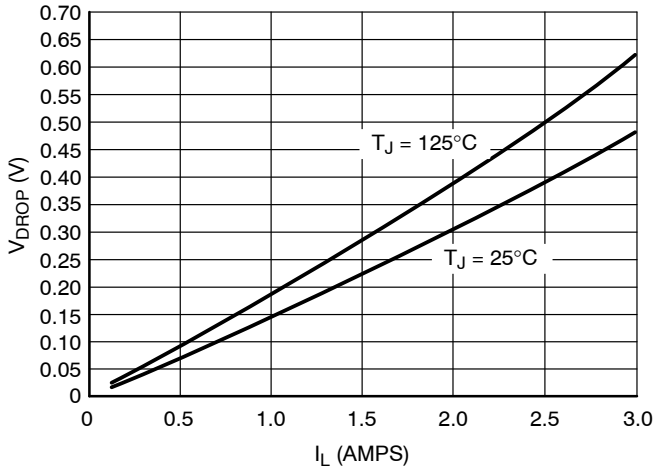


Figure 2. V_{drop} vs. I_L @ $V_{\text{in}} = 2.5 \text{ V}$

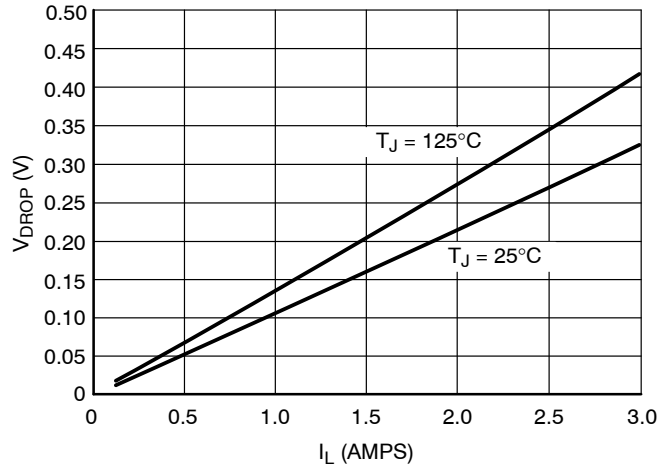


Figure 3. V_{drop} vs. I_L @ $V_{\text{in}} = 4.5 \text{ V}$

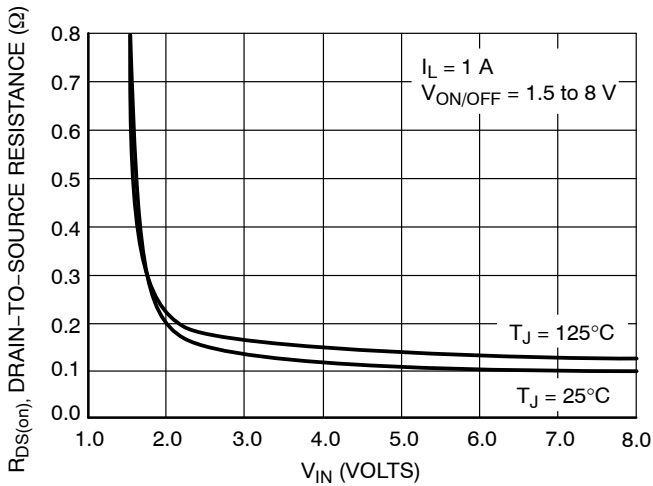


Figure 4. On-Resistance vs. Input Voltage

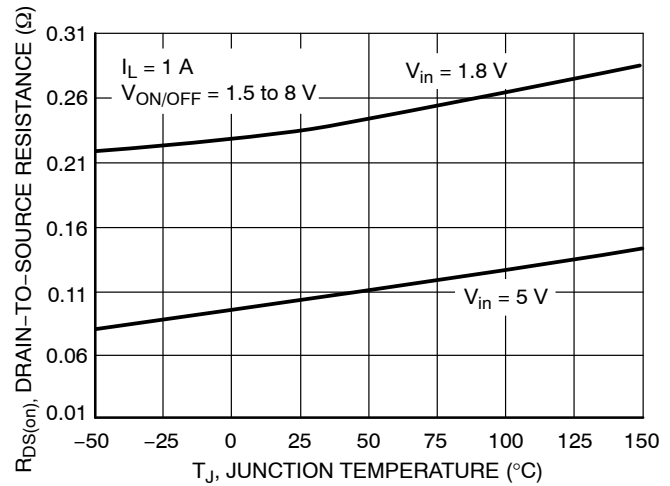


Figure 5. On-Resistance Variation with Temperature

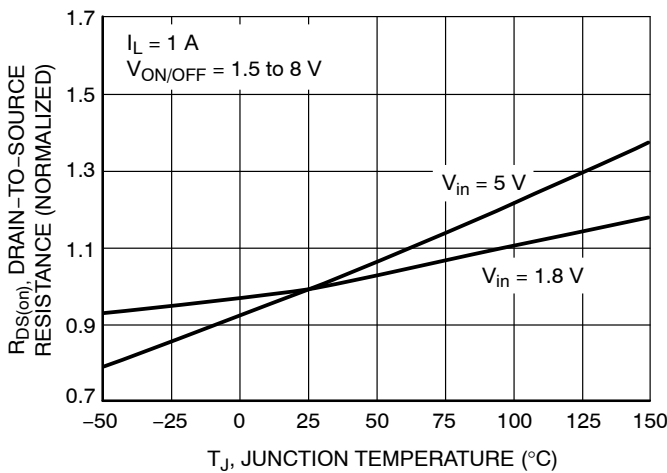


Figure 6. Normalized On-Resistance Variation with Temperature

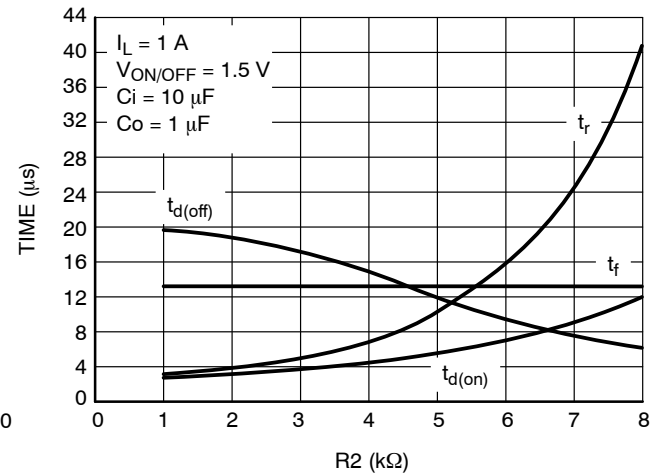


Figure 7. Switching Variation R_2 @ $V_{\text{in}} = 4.5 \text{ V}$, $R_1 = 20 \text{ k}\Omega$

NTJD1155L

TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

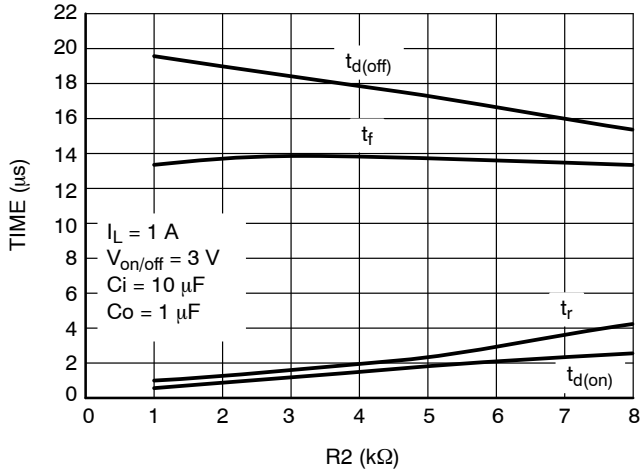


Figure 8. Switching Variation
R2 @ $V_{in} = 4.5\text{ V}$, $R_1 = 20\ \text{k}\Omega$

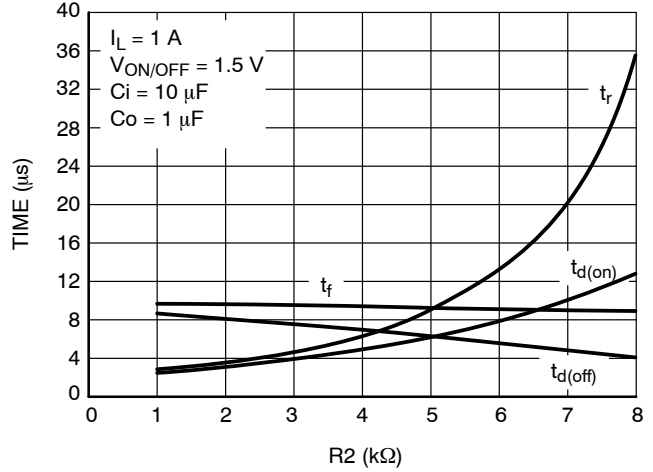


Figure 9. Switching Variation
R2 @ $V_{in} = 2.5\text{ V}$, $R_1 = 20\ \text{k}\Omega$

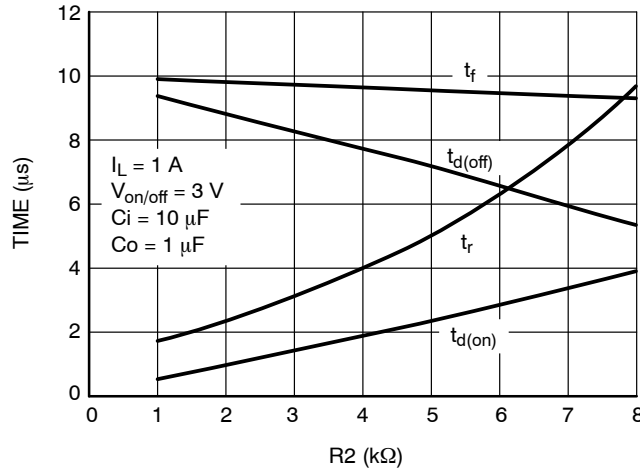


Figure 10. Switching Variation
R2 @ $V_{in} = 2.5\text{ V}$, $R_1 = 20\ \text{k}\Omega$

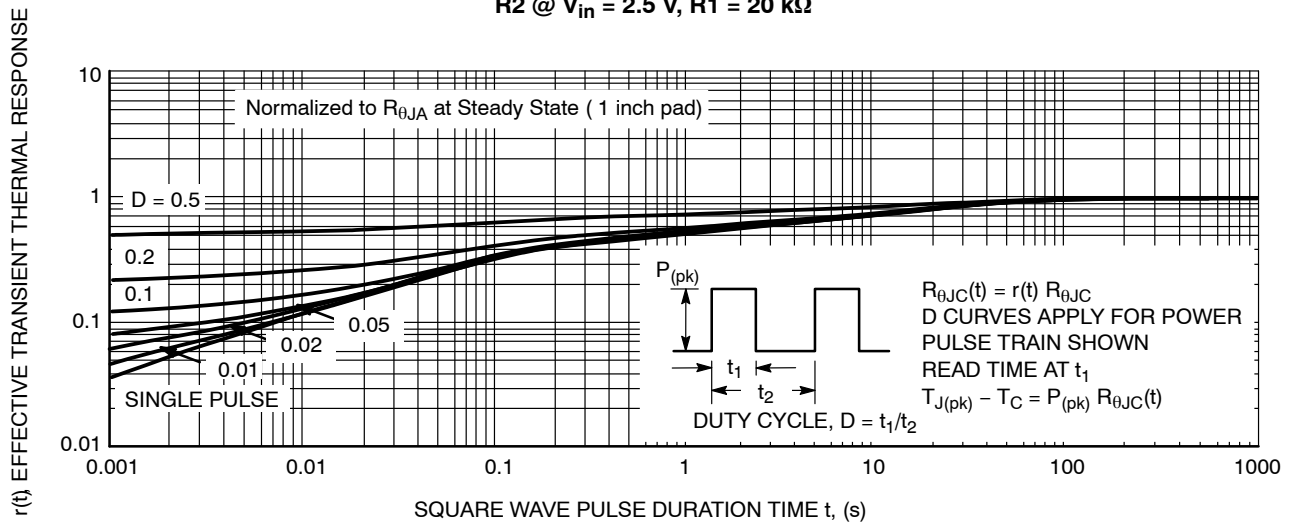


Figure 11. FET Thermal Response

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

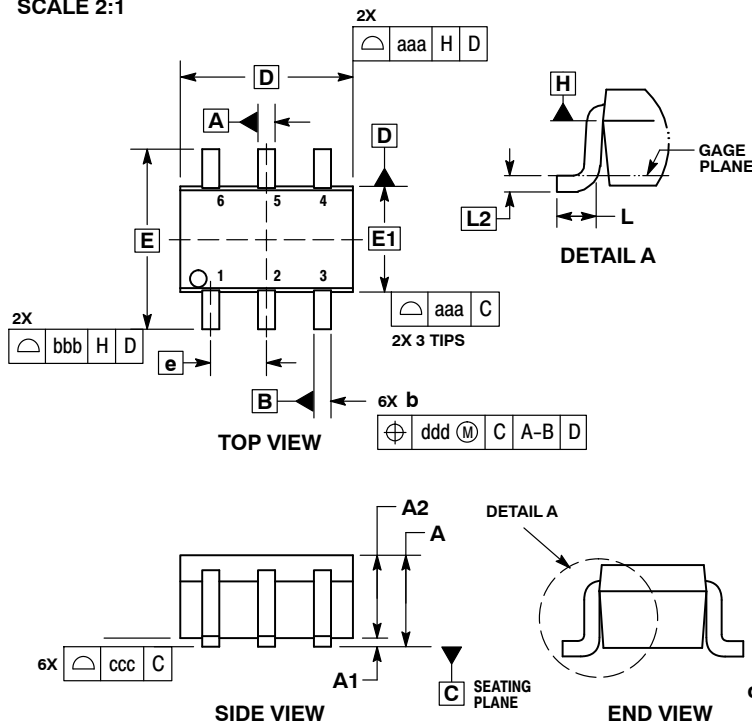
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1
SCALE 2:1

SC-88/SC70-6/SOT-363
CASE 419B-02
ISSUE Y

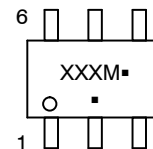
DATE 11 DEC 2012



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
 4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
 5. DATUMS A AND B ARE DETERMINED AT DATUM H.
 6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
 7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	---	---	1.10	---	---	0.043
A1	0.00	---	0.10	0.000	---	0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
C	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
ccc	0.10			0.004		
ddd	0.10			0.004		

GENERIC MARKING DIAGRAM*



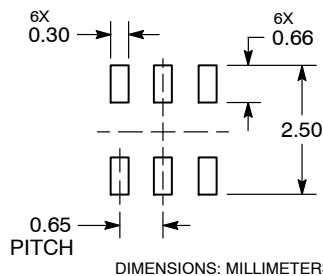
- XXX = Specific Device Code
- M = Date Code*
- = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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SC-88/SC70-6/SOT-363
CASE 419B-02
ISSUE Y

DATE 11 DEC 2012

STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13: PIN 1. ANODE 2. N/C 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 14: PIN 1. VREF 2. GND 3. GND 4. IOUT 5. VEN 6. VCC	STYLE 15: PIN 1. ANODE 1 2. ANODE 2 3. ANODE 3 4. CATHODE 3 5. CATHODE 2 6. CATHODE 1	STYLE 16: PIN 1. BASE 1 2. EMITTER 2 3. COLLECTOR 2 4. BASE 2 5. EMITTER 1 6. COLLECTOR 1	STYLE 17: PIN 1. BASE 1 2. EMITTER 1 3. COLLECTOR 2 4. BASE 2 5. EMITTER 2 6. COLLECTOR 1	STYLE 18: PIN 1. VIN1 2. VCC 3. VOUT2 4. VIN2 5. GND 6. VOUT1
STYLE 19: PIN 1. IOUT 2. GND 3. GND 4. V CC 5. V EN 6. V REF	STYLE 20: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR	STYLE 21: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. N/C 6. CATHODE 1	STYLE 22: PIN 1. D1 (i) 2. GND 3. D2 (i) 4. D2 (c) 5. VBUS 6. D1 (c)	STYLE 23: PIN 1. Vn 2. CH1 3. Vp 4. N/C 5. CH2 6. N/C	STYLE 24: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
STYLE 25: PIN 1. BASE 1 2. CATHODE 3. COLLECTOR 2 4. BASE 2 5. EMITTER 6. COLLECTOR 1	STYLE 26: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	STYLE 27: PIN 1. BASE 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. EMITTER 2 6. COLLECTOR 2	STYLE 28: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	STYLE 29: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE/ANODE 6. CATHODE	STYLE 30: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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